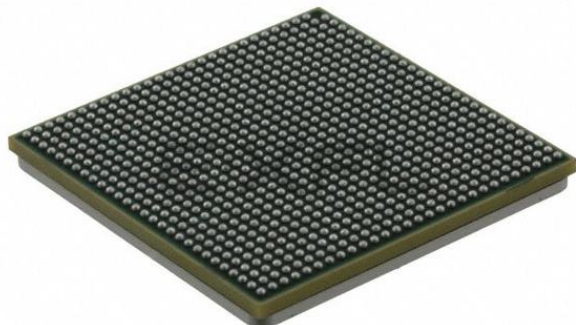




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Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Communications; CPM
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8555pxaqf

- 10 Mbps IEEE 802.3 MII
 - 1000 Mbps IEEE 802.3z TBI
 - 10/100/1000 Mbps RGMII/RTBI
- Full- and half-duplex support
- Buffer descriptors are backwards compatible with MPC8260 and MPC860T 10/100 programming models
- 9.6-Kbyte jumbo frame support
- RMON statistics support
- 2-Kbyte internal transmit and receive FIFOs
- MII management interface for control and status
- Programmable CRC generation and checking
- OCeaN switch fabric
 - Three-port crossbar packet switch
 - Reorders packets from a source based on priorities
 - Reorders packets to bypass blocked packets
 - Implements starvation avoidance algorithms
 - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
 - Four-channel controller
 - All channels accessible by both local and remote masters
 - Extended DMA functions (advanced chaining and striding capability)
 - Support for scatter and gather transfers
 - Misaligned transfer capability
 - Interrupt on completed segment, link, list, and error
 - Supports transfers to or from any local memory or I/O port
 - Selectable hardware-enforced coherency (snoop/no-snoop)
 - Ability to start and flow control each DMA channel from external 3-pin interface
 - Ability to launch DMA from single write transaction
- PCI Controllers
 - PCI 2.2 compatible
 - One 64-bit or two 32-bit PCI ports supported at 16 to 66 MHz
 - Host and agent mode support, 64-bit PCI port can be host or agent, if two 32-bit ports, only one can be an agent
 - 64-bit dual address cycle (DAC) support
 - Supports PCI-to-memory and memory-to-PCI streaming
 - Memory prefetching of PCI read accesses
 - Supports posting of processor-to-PCI and PCI-to-memory writes

Table 5. Typical I/O Power Dissipation

Interface	Parameters	GV _{DD} (2.5 V)	OV _{DD} (3.3 V)	LV _{DD} (3.3 V)	LV _{DD} (2.5 V)	Unit	Comments
DDR I/O	CCB = 200 MHz	0.46	—	—	—	W	—
	CCB = 266 MHz	0.59	—	—	—	W	—
	CCB = 300 MHz	0.66	—	—	—	W	—
	CCB = 333 MHz	0.73	—	—	—	W	—
PCI I/O	64b, 66 MHz	—	0.14	—	—	W	—
	64b, 33 MHz	—	0.08	—	—	W	—
	32b, 66 MHz	—	0.07	—	—	W	Multiply by 2 if using two 32b ports
	32b, 33 MHz	—	0.04	—	—	W	
Local Bus I/O	32b, 167 MHz	—	0.30	—	—	W	—
	32b, 133 MHz	—	0.24	—	—	W	—
	32b, 83 MHz	—	0.16	—	—	W	—
	32b, 66 MHz	—	0.13	—	—	W	—
	32b, 33 MHz	—	0.07	—	—	W	—
TSEC I/O	MII	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	0.07	—	W	
	RGMI or RTBI	—	—	—	0.04	W	
CPM - FCC	MII	—	0.015	—	—	W	—
	RMII	—	0.013	—	—	W	—
	HDLC 16 Mbps	—	0.009	—	—	W	—
	UTOPIA-8 SPHY	—	0.06	—	—	W	—
	UTOPIA-8 MPHY	—	0.1	—	—	W	—
	UTOPIA-16 SPHY	—	0.094	—	—	W	—
	UTOPIA-16 MPHY	—	0.135	—	—	W	—
CPM - SCC	HDLC 16 Mbps	—	0.004	—	—	W	—
TDMA or TDMB	Nibble Mode	—	0.01	—	—	W	—
TDMA or TDMB	Per Channel	—	0.005	—	—	W	Up to 4 TDM channels, multiply by number of TDM channels.

4 Clock Timing

4.1 System Clock Timing

Table 6 provides the system clock (SYSCLK) AC timing specifications for the MPC8555E.

Table 6. SYSCLK AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
SYSCLK frequency	f_{SYSCLK}	—	—	166	MHz	1
SYSCLK cycle time	t_{SYSCLK}	6.0	—	—	ns	—
SYSCLK rise and fall time	$t_{\text{KH}}, t_{\text{KL}}$	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	$t_{\text{KHK}}/t_{\text{SYSCLK}}$	40	—	60	%	3
SYSCLK jitter	—	—	—	+/- 150	ps	4, 5

Notes:

- Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies.
- Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.
- Timing is guaranteed by design and characterization.
- This represents the total input jitter—short term and long term—and is guaranteed by design.
- For spread spectrum clocking, guidelines are $\pm 1\%$ of the input frequency with a maximum of 60 kHz of modulation regardless of the input frequency.

4.2 TSEC Gigabit Reference Clock Timing

Table 7 provides the TSEC gigabit reference clock (EC_GTX_CLK125) AC timing specifications for the MPC8555E.

Table 7. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK125 rise time	t_{G125R}	—	—	1.0	ns	1
EC_GTX_CLK125 fall time	t_{G125F}	—	—	1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI RGMII, RTBI	$t_{\text{G125H}}/t_{\text{G125}}$	45 47	—	55 53	%	1, 2

Notes:

- Timing is guaranteed by design and characterization.
- EC_GTX_CLK125 is used to generate GTX clock for TSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47/53% as long as PHY device can tolerate the duty cycle generated by GTX_CLK of TSEC.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 13 provides the input AC timing specifications for the DDR SDRAM interface.

Table 13. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of $2.5\text{ V} \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	$MV_{REF} - 0.31$	V	—
AC input high voltage	V_{IH}	$MV_{REF} + 0.31$	$GV_{DD} + 0.3$	V	—
MDQS—MDQ/MECC input skew per byte For DDR = 333 MHz For DDR $\leq$ 266 MHz	t_{DISKEW}	—	750 1125	ps	1

Note:

- Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if $0 \leq n \leq 7$) or ECC (MECC[{0...7}] if $n = 8$).

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 14 and Table 15 provide the output AC timing specifications and measurement conditions for the DDR SDRAM interface.

Table 14. DDR SDRAM Output AC Timing Specifications for Source Synchronous Mode

At recommended operating conditions with GV_{DD} of $2.5\text{ V} \pm 5\%$.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/MCK[n] crossing)	t_{MCK}	6	10	ns	2
Skew between any MCK to ADDR/CMD 333 MHz 266 MHz 200 MHz	t_{AOSKEW}	–1000 –1100 –1200	200 300 400	ps	3
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHAS}	2.8 3.45 4.6	—	ns	4
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHAX}	2.0 2.65 3.8	—	ns	4
MCS(n) output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHCS}	2.8 3.45 4.6	—	ns	4

Table 14. DDR SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of 2.5 V $\pm$ 5%.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MCS(n) output hold with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHCX}	2.0 2.65 3.8	—	ns	4
MCK to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKMHM}	−0.9 −1.1 −1.2	0.3 0.5 0.6	ns	5
MDQ/MECC/MDM output setup with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDS} , t_{DDKLDS}	900 900 1200	—	ps	6
MDQ/MECC/MDM output hold with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDX} , t_{DDKLDX}	900 900 1200	—	ps	6
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.9$	$-0.5 \times t_{MCK} + 0.3$	ns	7
MDQS epilogue end	t_{DDKLME}	−0.9	0.3	ns	7

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)\ (reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
- All MCK/ $\overline{MCK}$ referenced measurements are made from the crossing of the two signals ± 0.1 V.
- In the source synchronous mode, MCK/ $\overline{MCK}$ can be shifted in 1/4 applied cycle increments through the Clock Control Register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
- ADDR/CMD includes all DDR SDRAM output signals except MCK/ $\overline{MCK}$, $\overline{MCS}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the Clock Control register is set to adjust the memory clocks by 1/2 applied cycle. The MCSx pins are separated from the ADDR/CMD (address and command) bus in the HW spec. This was separated because the MCSx pins typically have different loadings than the rest of the address and command bus, even though they have the same timings.
- Note that t_{DDKMHM} follows the symbol conventions described in note 1. For example, t_{DDKMHM} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). In the source synchronous mode, MDQS can launch later than MCK by 0.3 ns at the maximum. However, MCK may launch later than MDQS by as much as 0.9 ns. t_{DDKMHM} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. In source synchronous mode, this typically is set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. See the *MPC8555E PowerQUICC™ III Integrated Communications Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
- Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the MPC8555E.
- All outputs are referenced to the rising edge of MCK(n) at the pins of the MPC8555E. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

8.2.3.2 MII Receive AC Timing Specifications

Table 23 provides the MII receive AC timing specifications.

Table 23. MII Receive AC Timing Specifications

At recommended operating conditions with V_{DD} of $3.3\text{ V} \pm 5\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}^2	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise and fall time	$t_{MRXR}, t_{MRXF}^{2,3}$	1.0	—	4.0	ns

Notes:

- The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- Signal timings are measured at 0.7 V and 1.9 V voltage levels.
- Guaranteed by design.

Figure 11 shows the MII receive AC timing diagram.

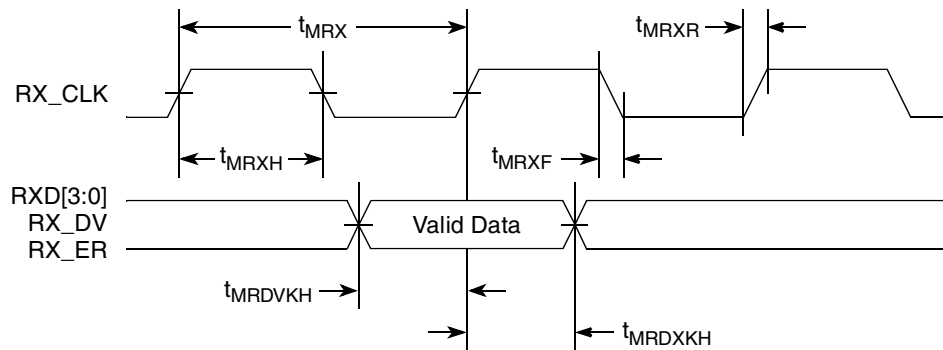


Figure 11. MII Receive AC Timing Diagram

8.2.4.2 TBI Receive AC Timing Specifications

Table 25 provides the TBI receive AC timing specifications.

Table 25. TBI Receive AC Timing Specifications

At recommended operating conditions with V_{DD} of 3.3 V $\pm$ 5%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
RX_CLK clock period	t_{TRX}		16.0		ns
RX_CLK skew	t_{SKTRX}	7.5	—	8.5	ns
RX_CLK duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%
RCG[9:0] setup time to rising RX_CLK	t_{TRDVKH}	2.5	—	—	ns
RCG[9:0] hold time to rising RX_CLK	t_{TRDXKH}	1.5	—	—	ns
RX_CLK clock rise time and fall time	t_{TRXR} , t_{TRXF} ^{2,3}	0.7	—	2.4	ns

Note:

- The symbols used for timing specifications herein follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)}$ (reference)(state) for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).
- Guaranteed by design.

Figure 13 shows the TBI receive AC timing diagram.

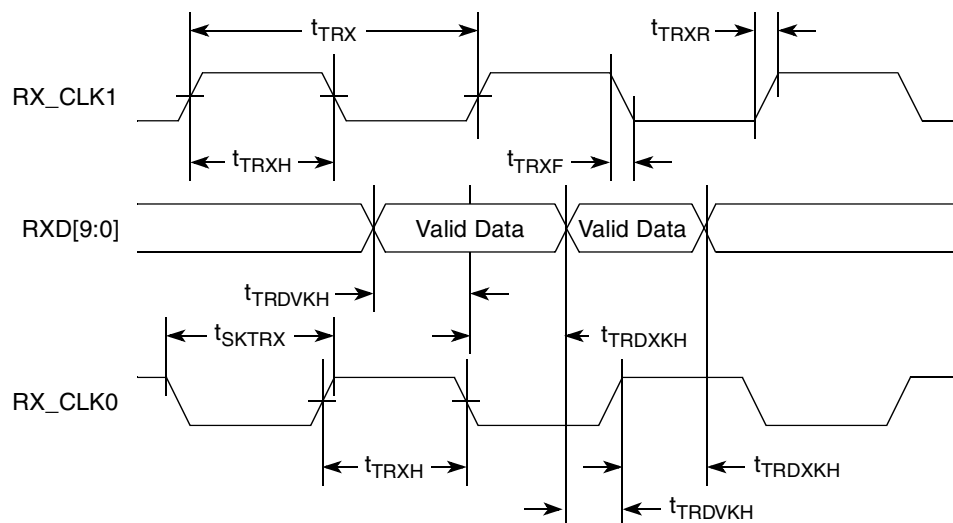


Figure 13. TBI Receive AC Timing Diagram

8.2.5 RGMII and RTBI AC Timing Specifications

Table 26 presents the RGMII and RTBI AC timing specifications.

Table 26. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with V_{DD} of 2.5 V $\pm$ 5%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT}^{5}	–500	0	500	ps
Data to clock input skew (at receiver) ²	t_{SKRGT}	1.0	—	2.8	ns
Clock cycle duration ³	t_{RGT}^{6}	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T ⁴	t_{RGTH}/t_{RGT}^{6}	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX ³	t_{RGTH}/t_{RGT}^{6}	40	50	60	%
Rise and fall times	$t_{RGTR}^{6,7}, t_{RGTF}^{6,7}$	—	—	0.75	ns

Notes:

- Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
- The RGMII specification requires that PC board designer add 1.5 ns or greater in trace delay to the RX_CLK in order to meet this specification. However, as stated above, this device functions with only 1.0 ns of delay.
- For 10 and 100 Mbps, t_{RGT} scales to 400 ns $\pm$ 40 ns and 40 ns $\pm$ 4 ns, respectively.
- Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.
- Guaranteed by characterization.
- Guaranteed by design.
- Signal timings are measured at 0.5 and 2.0 V voltage levels.

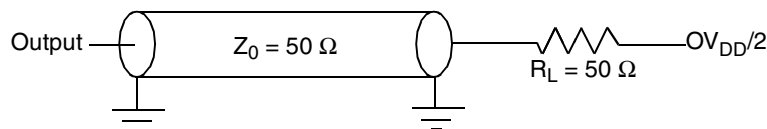
Table 31. Local Bus General Timing Parameters—DLL Bypassed (continued)

Parameter	Configuration ⁷	Symbol ¹	Min	Max	Unit	Notes
Local bus clock to address valid for LAD	$\overline{\text{LWE}}[0:1] = 00$	t_{LBKLOV3}	—	0.8	ns	3
	$\overline{\text{LWE}}[0:1] = 11$ (default)			2.3		
Output hold from local bus clock (except LAD/LDP and LALE)	$\overline{\text{LWE}}[0:1] = 00$	t_{LBKLOX1}	–2.7	—	ns	3
	$\overline{\text{LWE}}[0:1] = 11$ (default)		–1.8			
Output hold from local bus clock for LAD/LDP	$\overline{\text{LWE}}[0:1] = 00$	t_{LBKLOX2}	–2.7	—	ns	3
	$\overline{\text{LWE}}[0:1] = 11$ (default)		–1.8			
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$\overline{\text{LWE}}[0:1] = 00$	t_{LBKLOZ1}	—	1.0	ns	5
	$\overline{\text{LWE}}[0:1] = 11$ (default)			2.4		
Local bus clock to output high impedance for LAD/LDP	$\overline{\text{LWE}}[0:1] = 00$	t_{LBKLOZ2}	—	1.0	ns	5
	$\overline{\text{LWE}}[0:1] = 11$ (default)			2.4		

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for DLL enabled mode.
3. All signals are measured from $\text{OV}_{\text{DD}}/2$ of the rising edge of local bus clock for DLL bypass mode to $0.4 \times \text{OV}_{\text{DD}}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. The value of t_{LBOTOT} is defined as the sum of 1/2 or 1 ccb_clk cycle as programmed by LBCR[AHD], and the number of local bus buffer delays used as programmed at power-on reset with configuration pins $\overline{\text{LWE}}[0:1]$.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $\text{OV}_{\text{DD}}/2$.
8. Guaranteed by characterization.
9. Guaranteed by design.

Figure 16 provides the AC test load for the local bus.


Figure 16. Local Bus C Test Load

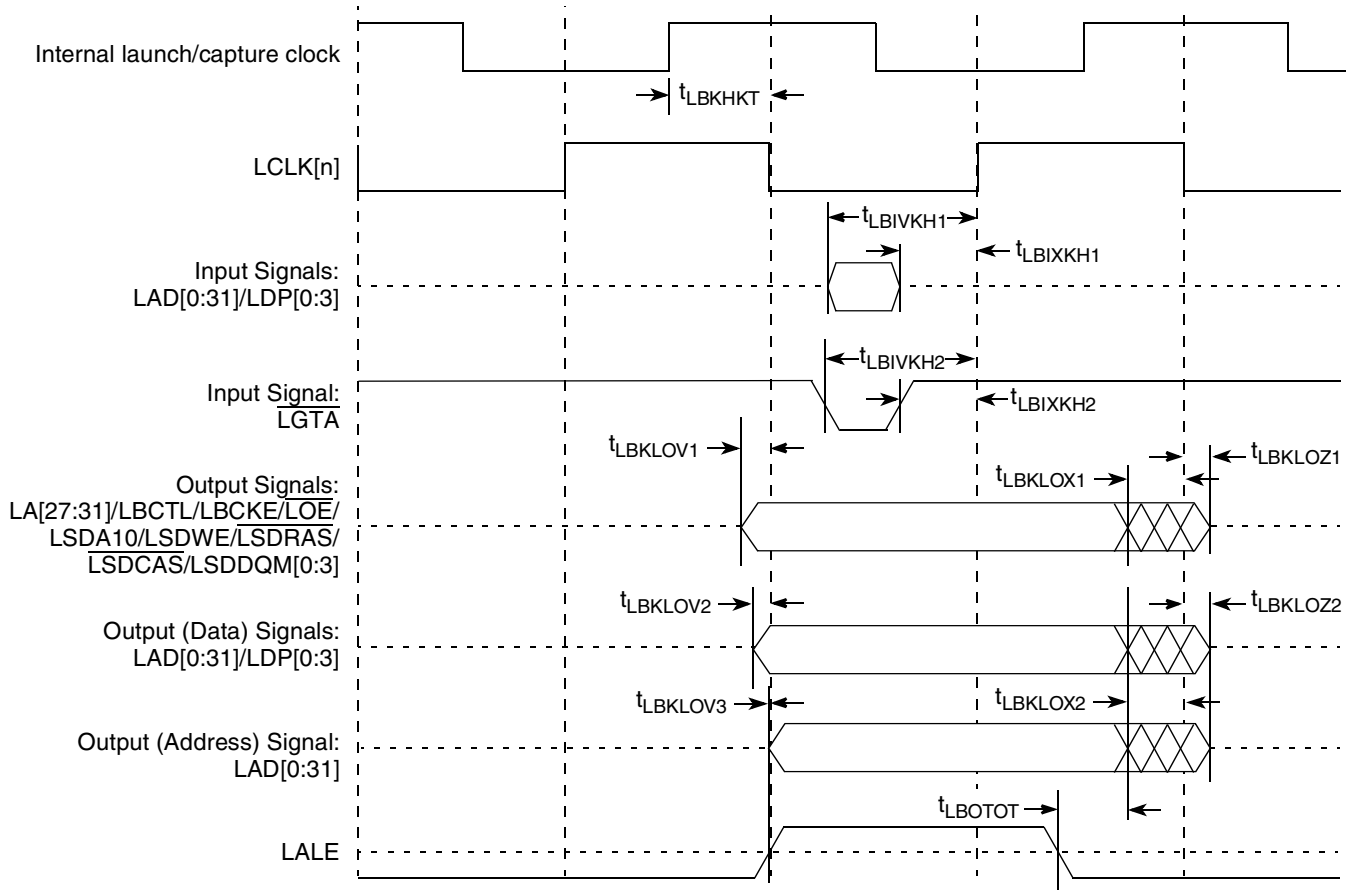


Figure 18. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

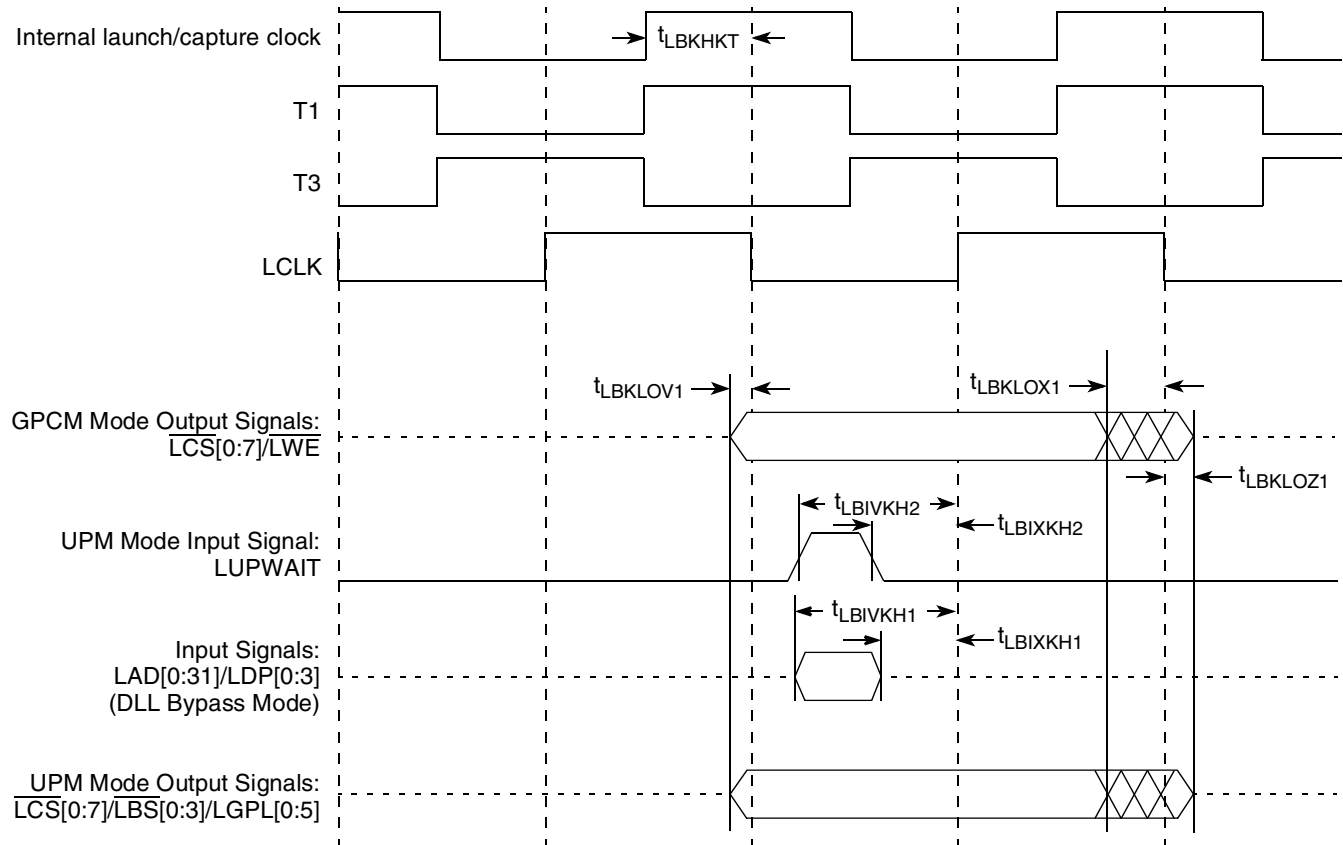


Figure 20. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Bypass Mode)

10 CPM

This section describes the DC and AC electrical specifications for the CPM of the MPC8555E.

10.1 CPM DC Electrical Characteristics

Table 32 provides the DC electrical characteristics for the CPM.

Table 32. CPM DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Input high voltage	V_{IH}		2.0	3.465	V	1
Input low voltage	V_{IL}		GND	0.8	V	1, 2
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V	1
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V	1
Output high voltage	V_{OH}	$I_{OH} = -2.0 \text{ mA}$	2.4	—	V	1
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V	1

Note:

1. This specification applies to the following pins: PA[0–31], PB[4–31], PC[0–31], and PD[4–31].
2. $V_{IL}(\text{max})$ for the IIC interface is 0.8 V rather than the 1.5 V specified in the IIC standard

10.2 CPM AC Timing Specifications

Table 33 and Table 34 provide the CPM input and output AC timing specifications, respectively.

NOTE: Rise/Fall Time on CPM Input Pins

It is recommended that the rise/fall time on CPM input pins should not exceed 5 ns. This should be enforced especially on clock signals. Rise time refers to signal transitions from 10% to 90% of VCC; fall time refers to transitions from 90% to 10% of VCC.

Table 33. CPM Input AC Timing Specifications ¹

Characteristic	Symbol ²	Min ³	Unit
FCC inputs—internal clock (NMSI) input setup time	t_{FIIVKH}	6	ns
FCC inputs—internal clock (NMSI) hold time	t_{FIIXKH}	0	ns
FCC inputs—external clock (NMSI) input setup time	t_{FEIVKH}	2.5	ns
FCC inputs—external clock (NMSI) hold time	t_{FEIXKH}^b	2	ns
SCC/SMC/SPI inputs—internal clock (NMSI) input setup time	t_{NIIVKH}	6	ns
SCC/SMC/SPI inputs—internal clock (NMSI) input hold time	t_{NIIXKH}	0	ns
SCC/SMC/SPI inputs—external clock (NMSI) input setup time	t_{NEIVKH}	4	ns
SCC/SMC/SPI inputs—external clock (NMSI) input hold time	t_{NEIXKH}	2	ns
TDM inputs/SI—input setup time	t_{TDIVKH}	4	ns

Table 33. CPM Input AC Timing Specifications ¹ (continued)

Characteristic	Symbol ²	Min ³	Unit
TDM inputs/SI—hold time	t_{TDIXKH}	3	ns
PIO inputs—input setup time	t_{PIIVKH}	8	ns
PIO inputs—input hold time	t_{PIIXKH}	1	ns
COL width high (FCC)	t_{FCCH}	1.5	CLK

Notes:

- Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
- The symbols used for timing specifications herein follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)\ (reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{FIIVKH} symbolizes the FCC inputs internal timing (FI) with respect to the time the input signals (I) reaching the valid state (V) relative to the reference clock t_{FCC} (K) going to the high (H) state or setup time. And t_{TDIXKH} symbolizes the TDM timing (TD) with respect to the time the input signals (I) reach the invalid state (X) relative to the reference clock t_{FCC} (K) going to the high (H) state or hold time.
- PIO and TIMER inputs and outputs are asynchronous to SYSCLK or any other externally visible clock. PIO/TIMER inputs are internally synchronized to the CPM internal clock. PIO/TIMER outputs should be treated as asynchronous.

Table 34. CPM Output AC Timing Specifications ¹

Characteristic	Symbol ²	Min	Max	Unit
FCC outputs—internal clock (NMSI) delay	t_{FIKHOX}	1	5.5	ns
FCC outputs—external clock (NMSI) delay	t_{FEKHOX}	2	8	ns
SCC/SMC/SPI outputs—internal clock (NMSI) delay	t_{NIKHOX}	0.5	10	ns
SCC/SMC/SPI outputs—external clock (NMSI) delay	t_{NEKHOX}	2	8	ns
TDM outputs/SI delay	t_{TDKHOX}	2.5	11	ns
PIO outputs delay	t_{PIKHOX}	1	11	ns

Notes:

- Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)\ (reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{FIKHOX} symbolizes the FCC inputs internal timing (FI) for the time t_{FCC} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Figure 23 provides the AC test load for the CPM.

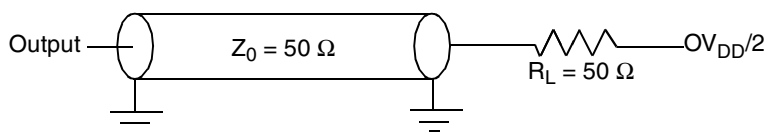
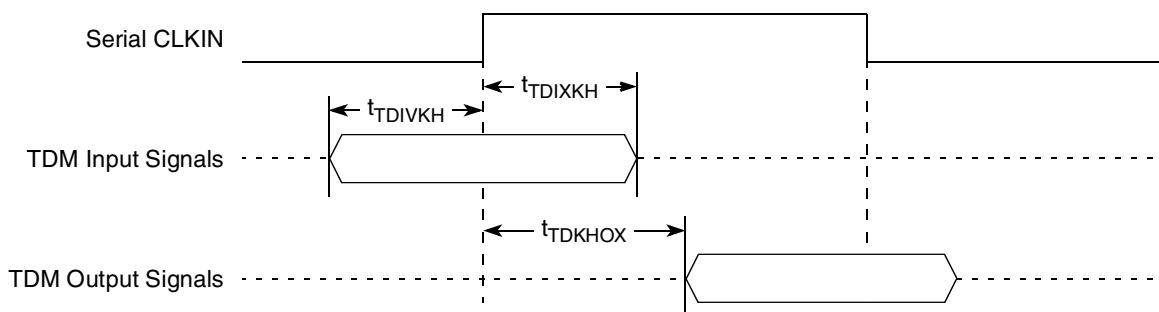

Figure 23. CPM AC Test Load

Figure 29 shows TDM input and output signals.



Note: There are 4 possible TDM timing conditions:

1. Input sampled on the rising edge and output driven on the rising edge (shown).
2. Input sampled on the rising edge and output driven on the falling edge.
3. Input sampled on the falling edge and output driven on the falling edge.
4. Input sampled on the falling edge and output driven on the rising edge.

Figure 29. TDM Signal AC Timing Diagram

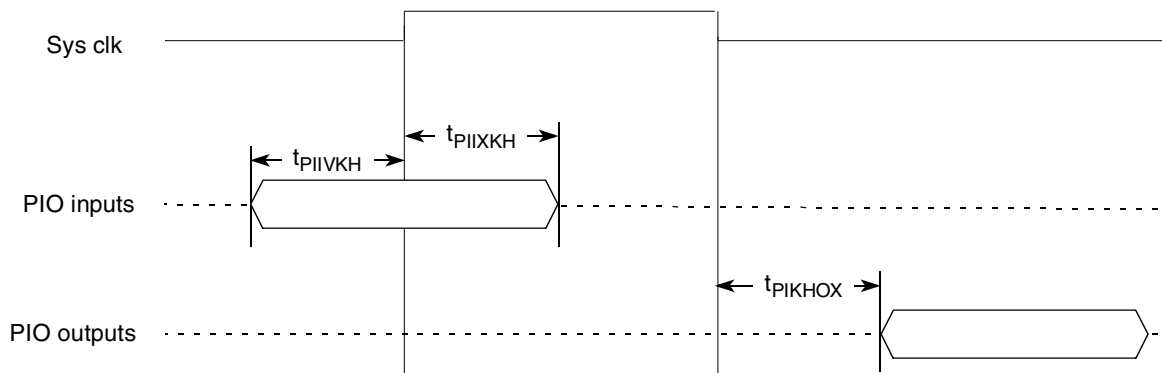


Figure 30. PIO Signal Diagram

10.3 CPM I2C AC Specification

Table 35. I2C Timing

Characteristic	Expression	All Frequencies		Unit
		Min	Max	
SCL clock frequency (slave)	f_{SCL}	0	$F_{MAX}^{(1)}$	Hz
SCL clock frequency (master)	f_{SCL}	BRGCLK/16512	BRGCLK/48	Hz
Bus free time between transmissions	t_{SDHDL}	$1/(2.2 * f_{SCL})$	-	s
Low period of SCL	t_{SCLCH}	$1/(2.2 * f_{SCL})$	-	s
High period of SCL	t_{SCHCL}	$1/(2.2 * f_{SCL})$	-	s
Start condition setup time ²	t_{SCHDL}	$2/(\text{divider} * f_{SCL})$	- ⁽²⁾	s
Start condition hold time ²	t_{SDLCL}	$3/(\text{divider} * f_{SCL})$	-	s
Data hold time ²	t_{SCLDX}	$2/(\text{divider} * f_{SCL})$	-	s
Data setup time ²	t_{SDVCH}	$3/(\text{divider} * f_{SCL})$	-	s
SDA/SCL rise time	t_{SRISE}	-	$1/(10 * f_{SCL})$	s

Figure 40 shows the PCI input AC timing conditions.

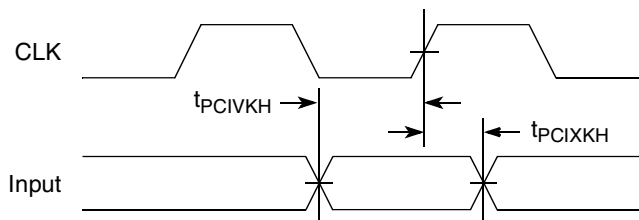


Figure 40. PCI Input AC Timing Measurement Conditions

Figure 41 shows the PCI output AC timing conditions.

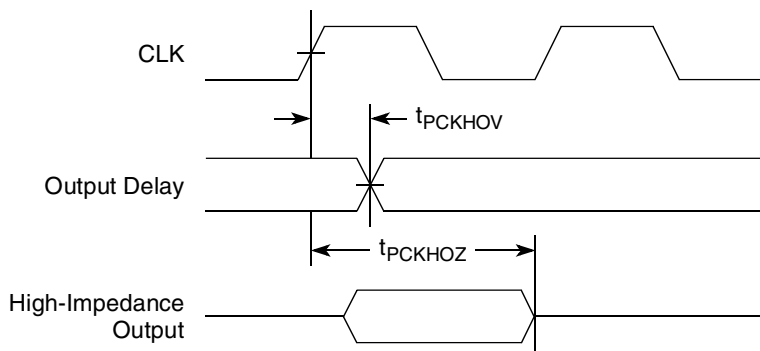


Figure 41. PCI Output AC Timing Measurement Condition

14 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions.

14.1 Package Parameters for the MPC8555E FC-PBGA

The package parameters are as provided in the following list. The package type is 29 mm × 29 mm, 783 flip chip plastic ball grid array (FC-PBGA).

Die size	8.7 mm × 9.3 mm × 0.75 mm
Package outline	29 mm × 29 mm
Interconnects	783
Pitch	1 mm
Minimum module height	3.07 mm
Maximum module height	3.75 mm
Solder Balls	62 Sn/36 Pb/2 Ag
Ball diameter (typical)	0.5 mm

Table 43. MPC8555E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI2_GNT[1:4]	AD18, AE18, AE19, AD19	O	OV _{DD}	5, 9
PCI2_IDSEL	AC22	I	OV _{DD}	—
PCI2_IRDY	AD20	I/O	OV _{DD}	2
PCI2_PERR	AC20	I/O	OV _{DD}	2
PCI2_REQ[0]	AD21	I/O	OV _{DD}	—
PCI2_REQ[1:4]	AE21, AD22, AE22, AC23	I	OV _{DD}	—
PCI2_SERR	AE20	I/O	OV _{DD}	2,4
PCI2_STOP	AC21	I/O	OV _{DD}	2
PCI2_TRDY	AC19	I/O	OV _{DD}	2
DDR SDRAM Memory Interface				
MDQ[0:63]	M26, L27, L22, K24, M24, M23, K27, K26, K22, J28, F26, E27, J26, J23, H26, G26, C26, E25, C24, E23, D26, C25, A24, D23, B23, F22, J21, G21, G22, D22, H21, E21, N18, J18, D18, L17, M18, L18, C18, A18, K17, K16, C16, B16, G17, L16, A16, L15, G15, E15, C14, K13, C15, D15, E14, D14, D13, E13, D12, A11, F13, H13, A13, B12	I/O	GV _{DD}	—
MECC[0:7]	N20, M20, L19, E19, C21, A21, G19, A19	I/O	GV _{DD}	—
MDM[0:8]	L24, H28, F24, L21, E18, E16, G14, B13, M19	O	GV _{DD}	—
MDQS[0:8]	L26, J25, D25, A22, H18, F16, F14, C13, C20	I/O	GV _{DD}	—
MBA[0:1]	B18, B19	O	GV _{DD}	—
MA[0:14]	N19, B21, F21, K21, M21, C23, A23, B24, H23, G24, K19, B25, D27, J14, J13	O	GV _{DD}	—
MWE	D17	O	GV _{DD}	—
MRAS	F17	O	GV _{DD}	—
MCAS	J16	O	GV _{DD}	—
MCS[0:3]	H16, G16, J15, H15	O	GV _{DD}	—
MCKE[0:1]	E26, E28	O	GV _{DD}	11
MCK[0:5]	J20, H25, A15, D20, F28, K14	O	GV _{DD}	—
MCK[0:5]	F20, G27, B15, E20, F27, L14	O	GV _{DD}	—
MSYNC_IN	M28	I	GV _{DD}	22
MSYNC_OUT	N28	O	GV _{DD}	22
Local Bus Controller Interface				
LA[27]	U18	O	OV _{DD}	5, 9

16.2.2 Internal Package Conduction Resistance

For the packaging technology, shown in Table 49, the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-board thermal resistance

Figure 45 depicts the primary heat transfer path for a package with an attached heat sink mounted to a printed-circuit board.

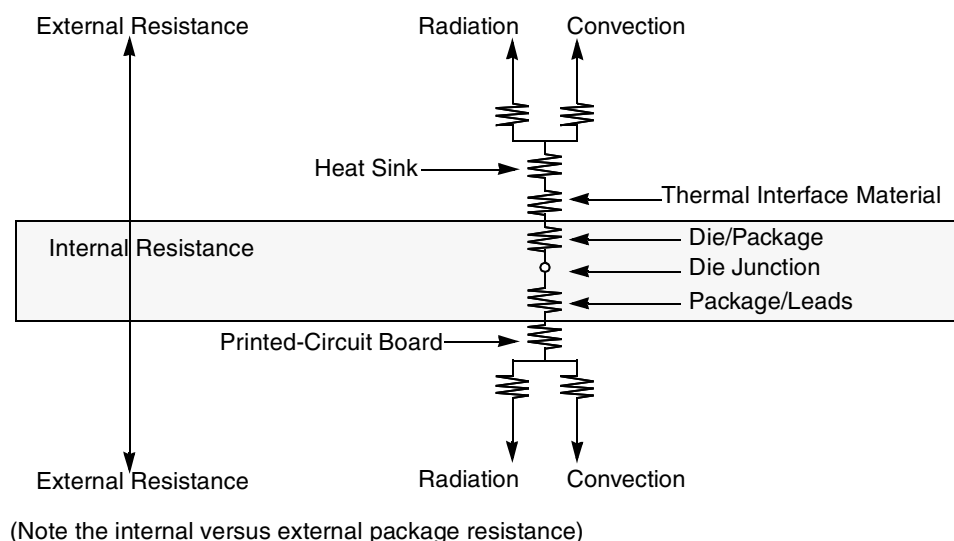


Figure 45. Package with Heat Sink Mounted to a Printed-Circuit Board

The heat sink removes most of the heat from the device. Heat generated on the active side of the chip is conducted through the silicon and through the lid, then through the heat sink attach material (or thermal interface material), and finally to the heat sink. The junction-to-case thermal resistance is low enough that the heat sink attach material and heat sink thermal resistance are the dominant terms.

16.2.3 Thermal Interface Materials

A thermal interface material is required at the package-to-heat sink interface to minimize the thermal contact resistance. For those applications where the heat sink is attached by spring clip mechanism, Figure 46 shows the thermal performance of three thin-sheet thermal-interface materials (silicone, graphite/oil, fluoroether oil), a bare joint, and a joint with thermal grease as a function of contact pressure. As shown, the performance of these thermal interface materials improves with increasing contact pressure. The use of thermal grease significantly reduces the interface thermal resistance. The bare joint results in a thermal resistance approximately six times greater than the thermal grease joint.

Heat sinks are attached to the package by means of a spring clip to holes in the printed-circuit board (see Figure 42). Therefore, the synthetic grease offers the best thermal performance, especially at the low interface pressure.

When removing the heat sink for re-work, it is preferable to slide the heat sink off slowly until the thermal interface material loses its grip. If the support fixture around the package prevents sliding off the heat sink,

Figure 50 shows the PLL power supply filter circuit.

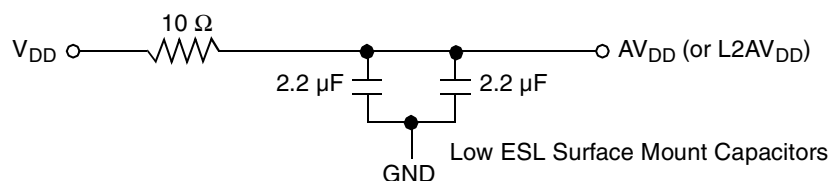


Figure 50. PLL Power Supply Filter Circuit

17.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the MPC8555E can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8555E system, and the MPC8555E itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} pins of the MPC8555E. These decoupling capacitors should receive their power from separate V_{DD} , OV_{DD} , GV_{DD} , LV_{DD} , and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 μF . Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 μF (AVX TPS tantalum or Sanyo OSCON).

17.4 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD} , GV_{DD} , or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD} , GV_{DD} , LV_{DD} , OV_{DD} , and GND pins of the MPC8555E.

17.5 Output Buffer DC Impedance

The MPC8555E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 51). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices.

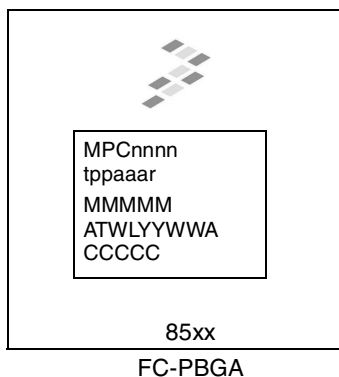
17.8.1 Termination of Unused Signals

If the JTAG interface and COP header are not used, Freescale recommends the following connections:

- $\overline{\text{TRST}}$ should be tied to $\overline{\text{HRESET}}$ through a 0 k Ω isolation resistor so that it is asserted when the system reset signal ($\overline{\text{HRESET}}$) is asserted, ensuring that the JTAG scan chain is initialized during the power-on reset flow. Freescale recommends that the COP header be designed into the system as shown in [Figure 53](#). If this is not possible, the isolation resistor allows future access to $\overline{\text{TRST}}$ in case a JTAG interface may need to be wired onto the system in future debug situations.
- Tie TCK to OV_{DD} through a 10 k Ω resistor. This prevents TCK from changing state and reading incorrect data into the device.
- No connection is required for TDI, TMS, or TDO.

19.2 Part Marking

Parts are marked as the example shown in [Figure 54](#).



Notes:

MMMMM is the 5-digit mask number.

ATWLYYWWA is the traceability code.

CCCCC is the country of assembly. This space is left blank if parts are assembled in the United States.

Figure 54. Part Marking for FC-PBGA Device